

Customer No.: 31561  
Docket No.: 10/709,469  
Application No.: 12129-US-PA

### Amendment

#### FOR THE SPECIFICATION

Please amend the following paragraphs as follows.

#### Paragraph [0013]

[0013] As shown in Fig. 2C, silicon nitride material is deposited on the surface of the trench 42 to form a silicon nitride layer 2526. As shown in Fig. 2D, an oxidation process is carried out and then the silicon nitride layer 25 is etched to form silicon nitride spacers 25a. Thereafter, a drain region 27 is formed in the substrate 20 at the bottom of the trench 42. Finally, polysilicon material is deposited into the trench 42 to form a polysilicon bit line 32.

#### Paragraph [0033]

[0033] As shown in Fig. 3B, the conductive layer 310 (shown in Fig. 3A) on the surface of the mask layer 304 is removed to form a conductive layer 310a in the trench 306. The conductive layer 310 (shown in Fig. 3A) above the mask layer 304 can be removed by etching back in a chemical-mechanical polishing operation, for example. Thereafter, a photolithographic and etching process (a patterning process) are carried out to form a trench 307 in the conductive layer 310a so that a pair of floating gates 314a and 314b are formed as shown in Fig. 3C. Afterwards, ions are implanted into the substrate 300 at the bottom of the trench 307 to form a first source/drain region 316 as shown in Fig. 3D.